ABSTRACT OF THE DISCLOSURE

This invention relates to a method for yield loss analysis of process steps of semi-conductor wafers having a plurality of dies, and more particularly relates to a defect inspection technique to determine a hit ratio, computation of yield impact contributions

5   for the defects, and determination of a kill ratio for a specific type of defect. Yield loss is estimated ultimately upon a choice of a defect density distribution function. A defect calibrated factor and a yield impact calibrated factor are introduced herein.